Icemos Technology Ltd Product Specification 1000.440001 Issue Date 25 August 2015 16:26

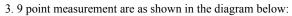
Part Number Customer

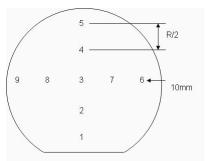
Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	499.90 +/- 6.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process
	7.0	Bow	<60.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	403.00 +/- 5.00 μm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	0.1-100 Ohmem	Wafer Vendor
	17.0	Backside Finish	Polished with lasermarking and Oxide.	Process conditions
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Device Wafer	
DeviceSilicon	21.0	Device Growth Method	FZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	94.90 +/- 0.50 μm	FTIR, 100% 9-Pt (note3)
	24.0	Distance to device silicon edge from wafer edge	<= 1.5mm	Typical by process
	25.0	Device Doping Type	Any	Wafer Vendor
	26.0	Device Dopant	Any	Wafer Vendor
	27.0	Device Resistivity	>10000 Ohmcm	Wafer Vendor
	28.0	Voids	0	Bright Light, 100% (note 2)
	29.0	Scratches	0	Bright Light, 100% (note 2)
	30.0	Haze	none	Bright Light, 100% (note 2)

Page 1 of 2 17/01/2019 www.icemostech.com

Part Number		Customer	
Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box:	Max 25	
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspec	tion performed using microscope scan as below. 5x objective.	
		pections performed exclude all wafer area outside the edge exclusion	on defined in Overall

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information